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## ARTICLES

Published on Web 00/00/0000

Direct Covalent Grafting of Conjugated Molecules onto Si,  
GaAs, and Pd Surfaces from Aryldiazonium SaltsMichael P. Stewart,<sup>†</sup> Francisco Maya,<sup>†</sup> Dmitry V. Kosynkin,<sup>†</sup> Shawn M. Dirk,<sup>†</sup>  
Josh J. Stapleton,<sup>‡</sup> Christine L. McGuinness,<sup>‡</sup> David L. Allara,<sup>\*,‡</sup> and  
James M. Tour<sup>\*,†</sup>

Contribution from the Departments of Chemistry and Mechanical Engineering and Materials  
Science, and Center for Nanoscale Science and Technology, MS-222, Rice University,  
Houston, Texas 77005, and Department of Chemistry and Department of Materials Science,  
Pennsylvania State University, University Park, Pennsylvania 16802

Received September 3, 2003; E-mail: tour@rice.edu

**Abstract:** Using aryldiazonium salts that are air-stable and easily synthesized, we describe here a one-step, room-temperature route to direct covalent bonds between  $\pi$ -conjugated organic molecules on three material surfaces: Si, GaAs, and Pd. The Si can be in the form of single crystal Si including heavily doped p-type Si, intrinsic Si, heavily doped n-type Si, on Si(111) and Si(100), and on n-type polycrystalline Si. The formation of the aryl-metal or aryl-semiconductor bond attachments was confirmed by corroborating evidence from ellipsometry, reflectance FTIR, XPS, cyclic voltammetry, and AFM analyses of the surface-grafted monolayers. A data-encompassing explanation for the mechanism suggests a diazonium activation by reduction at the open circuit potential, with aryl radical secondary products bonding to the surface. The synthetic details are included for preparing the surface-grafted monolayers and the precursor diazonium salts. This spontaneous diazonium activation reaction offers an attractive route to highly passivating, robust monolayers and multilayers on many surfaces that allow for strong bonds between carbon and surface atoms with molecular species that are near perpendicular to the surface.

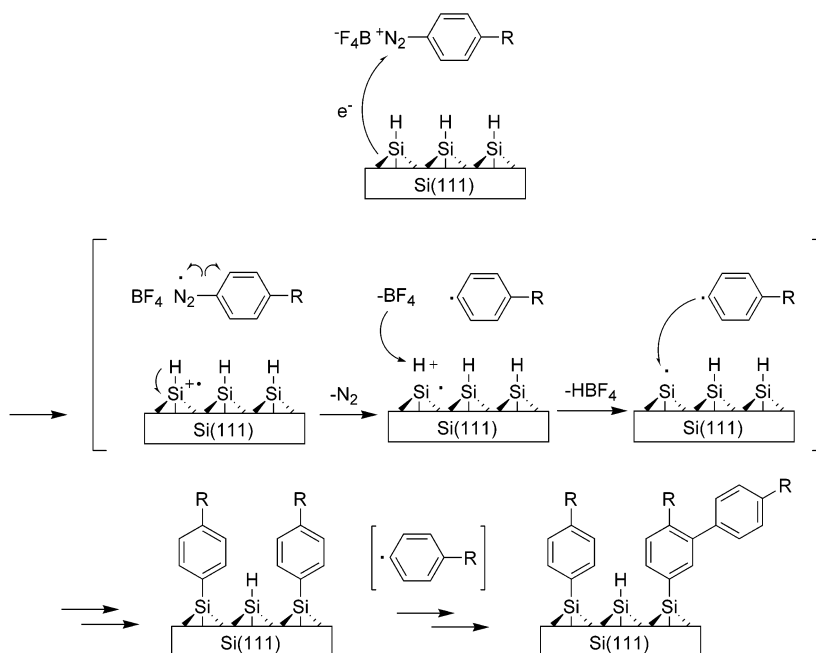
## Introduction

Recent advances in “wet” surface chemistry offer an increasingly sophisticated range of techniques for self-orienting molecular chemisorption on a wide variety of materials.<sup>1–3</sup> These new techniques expand the broad, general applicability of synthetic chemistry to the heterogeneous phase and improve the prospects of future “bottom-up” fabrication strategies in nanotechnology. Specifically, work related to the construction of post-CMOS hybrid electronic devices using chemical techniques and molecular components<sup>4–6</sup> to augment traditional fabrication schemes will require more control at the molecule/contact interfaces. In many experimental molecular electronic systems, molecules assembled between bulk metallic electrodes have chemical contacts that are highly polar, such as the sulfur-metal bond. This allows for undesired interfacial capacitance, possible electrochemical activity at the bond interface, and generally causes the molecule in the electrode gap to behave as a tunneling barrier.<sup>4</sup> If we are to take further advantage of the electronic properties of various chemical substituents on

these molecular devices, a less polar, more electronically continuous chemical interface must be identified.<sup>7</sup> A direct covalent bond, allowing stronger electronic coupling between the energy bands of a bulk contact and the frontier orbitals of a conjugated organic molecule, may allow for a greater deal of synthetic variation in device properties and make contact effects less dominant.<sup>8</sup> Using aryldiazonium salts that are air-stable and easily synthesized, we describe here a one-step, room-temperature route to direct covalent bonds between fully conjugated organic molecules and three technologically important material surfaces: Si, GaAs, and Pd.

The covalent surface chemistry of organic diazonium salts has been known for some time on electrode surfaces. In the best understood reactions, a diazonium salt in solution with an electrolyte such as tetrabutylammonium cation is reduced with an externally applied potential, typically at around  $-1$  V versus saturated calomel electrode (SCE), for reaction times of no more than a few minutes. The aryl radical intermediates that are locally formed rapidly react with the surface of the cathode. Electrochemical grafting of aryl groups onto carbon,<sup>9</sup> silicon,<sup>10</sup>

<sup>†</sup> Rice University.<sup>‡</sup> Pennsylvania State University.(1) Ullman, A. *Chem. Rev.* **1996**, *96*, 1533.(2) Buriak, J. M. *Chem. Rev.* **2002**, *102*, 1271.(3) Seker, F.; Meeker, K.; Kuech, T. F.; Ellis, A. B. *Chem. Rev.* **2000**, *100*, 2505.(4) Tour, J. M. *Molecular Electronics*; World Scientific: New Jersey, 2003.(5) Chen, J.; Reed, M. A.; Rawlett, A. M.; Tour, J. M. *Science* **1999**, *286*, 1550.(6) Reed, M. A.; Chen, J.; Rawlett, A. M.; Price, D. W.; Tour, J. M. *Appl. Phys. Lett.* **2001**, *78*, 3735.(7) Cahen, D.; Hodes, G. *Adv. Mater.* **2002**, *14*, 789.(8) Nitzan, A.; Ratner, M. A. *Science* **2003**, *960*, 153.(9) (a) Delamar, M.; Hitmi, R.; Pinson, J.; Saveant, J.-M. *J. Am. Chem. Soc.* **1992**, *114*, 5883. (b) Kuo, T. C.; McCreery, R. L.; Swain, G. M. *Electrochim. Solid-State Lett.* **1999**, *2*, 288.(10) (a) De Villeneuve, C. H.; Pinson, J.; Bernard, M. C.; Allongue, P. *J. Phys. Chem. B* **1997**, *101*, 2415. (b) Allongue, P.; de Villeneuve, C. H.; Pinson, J.; Ozanam, F.; Chazalviel, J.-N.; Wallart, X. *Electrochim. Acta* **1998**, *43*, 2791. (c) Allongue, P.; de Villeneuve, C. H.; Cherouvier, G.; Cortes, R.; Bernard, M.-C. *J. Electroanal. Chem.* **2003**, *550*, 161.

**Scheme 1.** Example of Spontaneous Diazonium Activation by a Hydrogen-Passivated Si(111) Surface<sup>a</sup>

<sup>a</sup> An electron transfer from the surface at the OCP generates a diazenyl radical, and then an aryl radical upon loss of N<sub>2</sub>. The complementary oxidative process generates a proton which eliminates as HBF<sub>4</sub>. The radical generation process results in side products such as reduced aromatics (by aryl radical attack of the Si–H surface) and the formation of covalently bound multilayers. FTIR evidence shows the loss of an average of 65% of the surface hydride residues in the process of aryl radical generation. The multilayer formation can be retarded by the addition of BHT in situ, which may intercept the excess aryl radicals before they can attack the nascent monolayer.

64 and iron<sup>11</sup> electrode surfaces from diazonium salt precursors  
 65 has been demonstrated previously by this kind of heterogeneous  
 66 phase reduction.<sup>12</sup> The grafting of similar groups onto carbon,<sup>13–15</sup>  
 67 carbon nanotube,<sup>16,17</sup> and metallic surfaces<sup>18,19</sup> has also been  
 68 carried out without electrochemical induction, using ancillary  
 69 reagents. We now report the activation of aryldiazonium salts<sup>20</sup>  
 70 alone, in the absence of an externally applied potential, or  
 71 exogenous reductant species, to assemble covalently bound  
 72 conjugated monolayers on hydride-passivated Si, GaAs, and Pd  
 73 surfaces. This chemistry has the ability to be applied to samples  
 74 where electrochemical means of surface activation are either  
 75 unwieldy or impossible, such as isolated, highly nonplanar, or  
 76 low-conductive substrates. Similar reactions might be possible  
 77 on many other surfaces and materials that have not yet been  
 78 studied, including many which have no known covalent attach-  
 79 ment chemistry with organic molecules.

## 80 Results and Discussion

81 A tentative mechanism for the spontaneous heterogeneous  
 82 activation of diazonium salts is tested and reconciled with our

experimental evidence. While specific details with regard to this  
 mechanism may differ from surface to surface, or remain  
 obscure, centrally we can propose a scheme in which the  
 diazonium salts are activated at the surface in the absence of  
 an externally applied potential, quickly forming a reactive  
 intermediate, followed by surface attachment. This is most likely  
 carried out by spontaneous electron transfer at the open circuit  
 potential (OCP) of the substrate material in solution, which leads  
 to the local generation of aryl radicals by loss of N<sub>2</sub>,<sup>21</sup> some  
 diffusion of these radicals within the solution, and ultimately  
 the formation of irreversible surface–molecule bonds (Scheme  
 1).

Silicon hydride-passivated surfaces are known to activate  
 metal salts<sup>22</sup> and dioxygen<sup>23</sup> in solution, undergoing OCP  
 reduction at the Si(111):H electrode surface. This activation is  
 also considered to be a corrosion potential, as there is a  
 concomitant oxidation of the silicon surface in concert with the  
 reduction. Yet, this technique diminishes incorporation of  
 oxygen into the surface structure (in the form of SiO<sub>2</sub> for Si, or  
 Ga<sub>2</sub>O<sub>3</sub> and As<sub>2</sub>O<sub>3</sub> for GaAs) and nonisolated contaminants such  
 as HBF<sub>4</sub>. This lack of contamination of the interface is  
 corroborated by X-ray photoelectron spectroscopy (XPS) and  
 by atomic force microscopy (AFM) studies which show that  
 surface roughening<sup>24</sup> is minimal (vide infra). The required  
 complementary reverse electron transfer for the diazonium  
 activation at OCP has not been identified, but possibilities  
 include backside surface decomposition and the presence of trace  
 redox species in solution.

- (11) (a) Adenier, A.; Bernard, M.-C.; Chehimi, M. C.; Cabat-Deliry, E.; Desbat, B.; Fagebaume, O.; Pinson, J.; Podovoric, F. *J. Am. Chem. Soc.* **2001**, *123*, 4541. (b) Chausse, A.; Chehimi, M. M.; Karsi, N.; Pinson, J.; Podvoric, F.; Vautrin-Ul, C. *Chem. Mater.* **2002**, *14*, 392. (c) Boukerma, K.; Chehimi, M. M.; Pinson, J.; Blomfield, C. *Langmuir* **2003**, *19*, 6333.  
 (12) Allongue, P.; Delamar, M.; Desarmot, G.; Fagebaume, O.; Hitmi, R.; Pinson, J.; Saveant, J.-M. *J. Am. Chem. Soc.* **1997**, *119*, 201.  
 (13) Belmont, J. A. U.S. Patent 5,554,739.  
 (14) Ranganathan, S.; Steidel, I.; Anariba, F.; McCreery, R. L. *Nano Lett.* **2001**, *1*, 491.  
 (15) Combellas, C.; Kanoufi, F.; Mazouzi, D.; Thiébaud, A.; Bertrand, P.; Médard, N. *Polymer* **2003**, *44*, 19.  
 (16) Bahr, J. L.; Tour, J. M. *Chem. Mater.* **2001**, *13*, 3823.  
 (17) Dyke, C. A.; Tour, J. M. *J. Am. Chem. Soc.* **2003**, *125*, 1156.  
 (18) Fan, F. F.; Yang, J.; Dirk, S. M.; Price, D. W.; Kosynkin, D. V.; Tour, J. M.; Bard, A. J. *J. Am. Chem. Soc.* **2001**, *123*, 2454.  
 (19) Kosynkin, D. V.; Yang, J.; Tour, J. M. *Mater. Res. Symp. Proc.* **2001**, *660*, JJ3.5.1.  
 (20) Kosynkin, D. V.; Tour, J. M. *Org. Lett.* **2001**, *3*, 993.

- (21) Zollinger, H. *Diazo Chemistry I: Aromatic and Heteroaromatic Compounds*; VCH: Weinheim, 1994; p 188.  
 (22) Gorostiza, P.; Kulandainathan, M. A.; Diaz, R.; Sanz, F.; Allongue, P.; Morante, J. R. *J. Electrochem. Soc.* **2000**, *147*, 1026.  
 (23) Wade, C. P.; Chidsey, C. E. D. *Appl. Phys. Lett.* **1997**, *71*, 1679.  
 (24) Magagnin, L.; Maboudian, R.; Carraro, C. *J. Phys. Chem. B* **2002**, *106*, 401.

**Table 1.** Calculated and Observed Layer Thicknesses (in nm) for Diazonium-Reacted Surfaces for Three Different Chemisorbates I, III, and III<sup>a</sup>

	I	II	III
calculated length without surface bond	1.1	1.8	1.1
n <sup>2+</sup> -Si(111):H 1 h	1.3 ± 0.3	2.1 ± 0.5	1.4 ± 0.2
n <sup>2+</sup> -Si(111):H 6 h	2.5 ± 0.5	3.1 ± 0.8	2.1 ± 0.4
n <sup>2+</sup> -Si(111):H 6 h with 0.01 M BHT	1.8 ± 0.1	2.2 ± 0.2	1.9 ± 0.2
GaAs(100) 1 h	1.0 ± 0.2	1.7 ± 0.3	0.9 ± 0.2
GaAs(100) 6 h	2.8 ± 0.4	3.0 ± 0.9	2.5 ± 0.7
GaAs(100) 6 h with 0.01 M BHT	1.8 ± 0.2	2.9 ± 0.2	1.9 ± 0.2
Pd 1 h	1.4 ± 0.4	2.2 ± 0.3	1.4 ± 0.3
Pd 6 h	2.1 ± 0.4	3.3 ± 0.7	2.3 ± 0.7
Pd 6 h with 0.01 M BHT	1.5 ± 0.1	2.2 ± 0.1	1.8 ± 0.2

<sup>a</sup> Calculated length values are from Alchemy III software and do not include the organometallic bond length. All experimental values given are the average of three identically prepared samples for reactions of 0.5 mM solutions of diazonium salts in CH<sub>3</sub>CN, reacted in the dark inside an inert atmosphere glovebox for the indicated time period. A monolayer of the chemisorbates tends to form within 1 h, followed by multilayer formation over extended time periods. Generally, the most defect-free layers were formed after a reaction time of 1 h, based on CV measurements. The presence of 0.01 M BHT in situ improves the layer quality by retarding the formation of multilayers over extended periods but does prevent the reaction from occurring entirely.

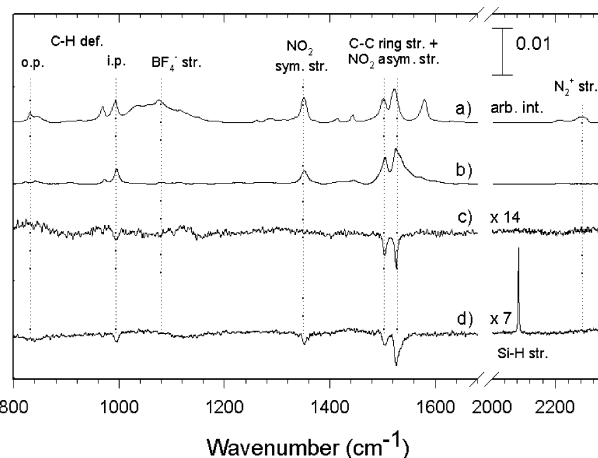
Because the presence of an inert passivating layer, such as the native oxide of Si or GaAs, prevents any stable layers from forming, the native oxides must be removed by fluoride or ammonium hydroxide to see any reaction. This implies that a chemically reactive surface plays a part in the activation or bond-forming mechanism. Moreover, the reaction shows sensitivity to the presence of a radical scavenger like butylated hydroxytoluene (BHT), added in small amounts (ca. 0.1 mM), which retards the formation of organic multilayers but does not prevent the reaction from occurring (Table 1). A high-quality monolayer of the chemisorbates tends to be complete within 2 h under nitrogen atmosphere, according to ellipsometry and cyclic voltammetry (CV). The observed ellipsometric thickness for the monolayer corresponds to a near-vertical single molecular length. In light of these results regarding the BHT retarding-effect, it is implied that the multilayer formation on Si, Pd, and GaAs surfaces is radical-mediated.

For the assembly procedure, a cleaned surface is exposed to a solution of the diazonium salt (I–VI) in anhydrous acetonitrile (CH<sub>3</sub>CN), in the dark, over a period of 2 h under an inert atmosphere. The presence of atmospheric oxygen seems to promote the formation of disordered multilayers, which have been observed in the electrochemical reactions as well.<sup>25</sup> Pd samples are freshly sputtered and used without further treatment, and GaAs samples are chemically cleaned<sup>26,27</sup> with concentrated NH<sub>4</sub>OH, which results in a metastable, stoichiometric surface

(25) (a) Kariuki, J. K.; McDermott, M. T. *Langmuir* **2001**, *17*, 5947. (b) Anariba, F.; DuVall, S. H.; McCreery, R. L. *Anal. Chem.* **2003**, *75*, 3837.

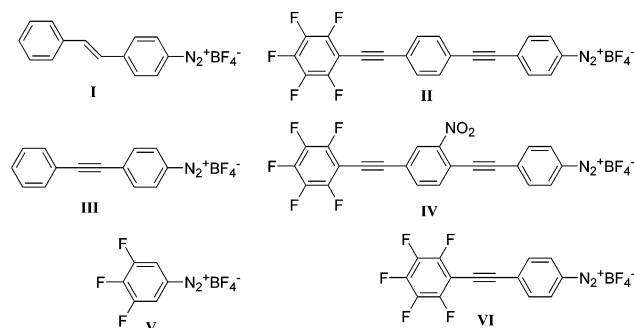
(26) Nakagawa, O. S.; Ashok, S.; Sheen, C. W.; Mårtensson, J.; Allara, D. L. *Jpn. J. Appl. Phys.* **1991**, *30*, 3759.

(27) Sheen, C. W.; Shi, J. X.; Mårtensson, J.; Allara, D. L. *J. Am. Chem. Soc.* **1992**, *114*, 1514.



**Figure 1.** Reflectance FTIR spectra of ultrathin layers on 2'' wafers: (a) compound IV (KBr pellet), (b) polycrystalline Pd wafer reacted with IV, (c) n-type GaAs(100) wafer reacted with IV, (d) n<sup>2+</sup>-type Si(111):H wafer reacted with IV. The spectra show a selective enhancement of vibrational modes based on molecular orientation. In Figure 1c, molecules attached to GaAs(100) show less enhancement of the ν<sub>s</sub>(NO<sub>2</sub>) mode, most likely because of a slight tilt with respect to the surface. All surface samples were checked by ellipsometry for monolayer thickness (2 ± 0.2 nm on <111>, around 1.7 nm on <100>).

that is free of As or Ga oxides. The reaction with diazonium salts has been successfully carried out on a wide range of oxide-free hydride-passivated<sup>28</sup> silicon surfaces: single crystal Si including doped p-type Si, intrinsic Si, heavily doped n-type Si, Si(111) and Si(100), and on n-type polycrystalline Si.

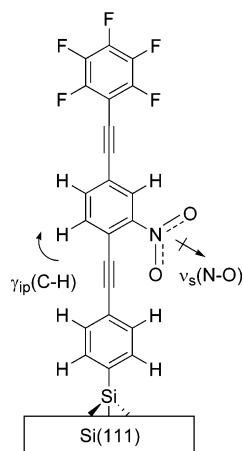


To analyze the samples by Fourier transform infrared (FTIR), a grazing angle experiment was used with heavily doped Si and GaAs wafers and sputtered polycrystalline Pd on Si wafers. The FTIR spectra in Figure 1b–d show structural features related to the organic chemisorbate IV and provide qualitative information about its alignment with respect to the surface. IR reflectance spectra with p-polarized light at angles of incidence greater than Brewster's angle on dielectric surfaces, such as Si and GaAs (Figure 1c and d), tend to give negative absorbance peaks.<sup>29</sup> As compared to the KBr pellet spectrum of the diazonium salt IV (Figure 1a), where all orientations relative to the IR source are present, only those vibrations with a component normal to the surface are present in the monolayer spectra (represented from 1b to d).

This provides important information about how the molecules are aligned on the surface. The most prominent features are the in-plane ring breathing ν(C=C) modes at around 1525 and 1503

(28) Higashi, G. S.; Chabal, Y. J.; Trucks, G. W.; Raghavachari, K. *Appl. Phys. Lett.* **1990**, *56*, 656.

(29) Brunner, H.; Mayer, U.; Hoffman, H. *Appl. Spectrosc.* **1997**, *51*, 209.



159  $\text{cm}^{-1}$ , the antisymmetric  $\text{NO}_2$  stretch  $\nu_{\text{as}}(\text{NO}_2)$  mode at 1518  
 160  $\text{cm}^{-1}$  (partially obscured by the ring breathing mode at 1525  
 161  $\text{cm}^{-1}$ ), the symmetric  $\text{NO}_2$  stretch  $\nu_{\text{s}}(\text{NO}_2)$  mode at 1351  $\text{cm}^{-1}$ ,  
 162 and an in-plane aromatic C–H deformation  $\gamma_{\text{ip}}(\text{C–H})$  mode at  
 163 995  $\text{cm}^{-1}$ , which are seen in FTIR spectra of all three substrates;  
 164 the strong breathing mode near 1600  $\text{cm}^{-1}$  and an out-of-plane  
 165 aromatic C–H deformation  $\gamma_{\text{op}}(\text{C–H})$  mode at 825  $\text{cm}^{-1}$  are  
 166 present only in very weak intensity. The notable absence of  
 167 vibrational features related to the diazonium tetrafluoroborate  
 168 moiety on any of the samples, such as the  $\nu(\text{N}\equiv\text{N}^+)$  peak near  
 169 2280  $\text{cm}^{-1}$  and the strong and broad  $\nu(\text{BF}_4^-)$  mode expected at  
 170 around 1050  $\text{cm}^{-1}$  (Figure 1a), suggests that it is no longer  
 171 associated with the molecular layer. In Figure 1d, the spectrum  
 172 for the assembly of **IV** on Si(111):H, loss of surface hydride  
 173 residues is evident in a upward sharp  $\nu(\text{Si–H})$  stretching peak  
 174 at 2080  $\text{cm}^{-1}$ . The peak is inverted as compared to the molecular  
 175 signatures because a freshly hydride-terminated Si(111) wafer  
 176 is used as the reference sample. No silicon oxide signal is seen  
 177 in the spectrum; if present, a large  $\nu(\text{SiO}_x)$  peak around 1050  
 178  $\text{cm}^{-1}$  and an oxide-back-bonded  $\nu(\text{O}_x\text{Si–H})$  stretching peak at  
 179 around 2220  $\text{cm}^{-1}$  would be visible. Comparison of the Si  
 180 stretching regions of Si(111):H samples before and after reaction  
 181 shows an average 65% net consumption of the surface hydride,  
 182 indicating a maximal surface coverage on the part of the phenyl  
 183 groups.<sup>10c</sup> The hydride groups are possibly lost during the  
 184 grafting reaction by aryl radical abstraction (leading to soluble  
 185 side products) or by elimination as  $\text{HBF}_4$ . In either case, it is  
 186 direct proof that the activation of the diazonium salt and the  
 187 subsequent formation of organic layers on the silicon surface  
 188 cause chemical changes at the Si–H level of the Si(111):H  
 189 surface without incurring direct oxidation.

190 Oxide-free organic functionalization of the Si surface is  
 191 corroborated by XPS. A Si(111) sample reacted with **II** shows  
 192 two peaks in the C 1s region, the smaller of the two being from  
 193 the fluorocarbon terminus appearing at higher binding energy  
 194 (Figure 2a), and a single peak in the F 1s region around 688.3  
 195 eV (see Supporting Information) corresponding to the penta-  
 196 fluorophenyl terminus. Clearly, the absence of the  $\text{BF}_4^-$   
 197 counterion which composes part of the diazonium salt (typically  
 198 appearing at about 686.5 eV) is evidenced. There is no N 1s  
 199 signal for  $-\text{N}_2^+$  (approximately 403.8 eV) in any of the spectra,  
 200 indicating that the diazonium moiety has been lost, although  
 201 assemblies of **IV** on all surfaces showed a clear signal for the  
 202  $-\text{NO}_2$  group at 406.0 eV. The Pd 3d region and Si 2p regions  
 203 (Figure 2b) of the XPS spectra indicate no oxide present in Pd

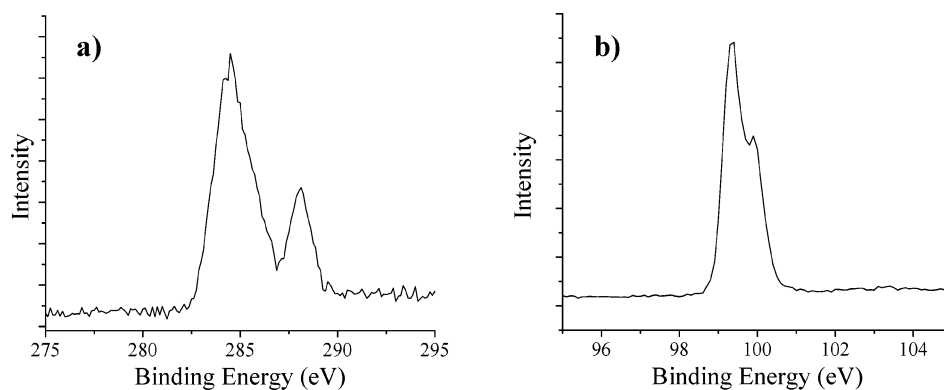
or Si samples, respectively. For GaAs samples, the As 3d region  
 sometimes shows a small amount of  $\text{As}^{\text{III}}$  oxide. If the samples  
 are prepared in  $\text{O}_2$ -containing atmospheres, the degree of  
 oxidation in Si and GaAs samples increases slightly. Samples  
 prepared with nonfluorinated diazonium salt **III** show only one  
 signal in the C 1s region and no signal in the F 1s region (see  
 Supporting Information).

Cyclic voltammetry (CV) analysis gives evidence of consid-  
 erable physical passivation against ion currents on the Si and  
 Pd surfaces reacted with **II** (Figure 3a and b). Our n-type GaAs  
 samples showed passivation for only a few sweeps. The currents  
 for the Pd and Si samples are both relatively potential-insensitive  
 against the  $\text{Fe}(\text{CN})_6^{3-/4-}$  couple, implying an overall low  
 concentration of defects and pinholes in the films. For the GaAs  
 samples, the putative Ga–C or As–C bond may not be  
 chemically stable enough to allow good passivation against ion  
 currents.

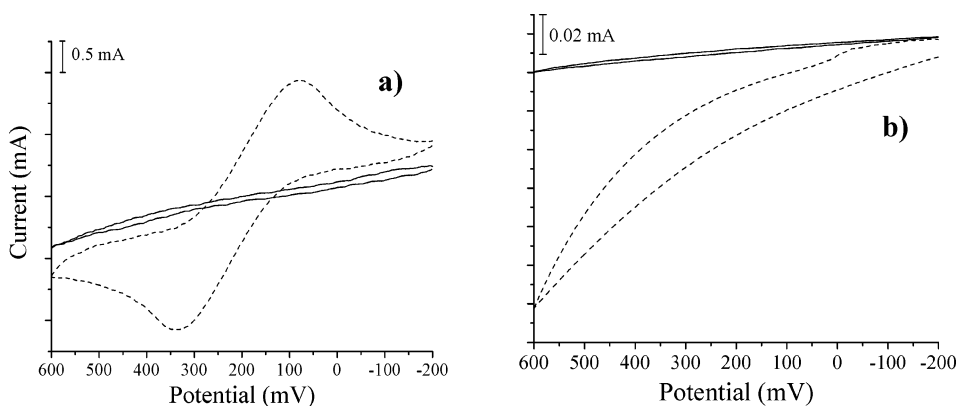
Because of the relative ease of preparing atomically flat Si-  
 (111):H surfaces<sup>30</sup> from wet treatment in 40%  $\text{NH}_4\text{F}$ , Si samples  
 reacted with diazonium compounds were checked for surface  
 roughness effects by AFM. Our freshly made Si(111):H samples  
 typically showed RMS roughness of 0.2 nm or less over 1  $\mu\text{m}^2$   
 areas, with atomic step edges being clearly visible. Samples  
 reacted with diazonium salts using the normal conditions (0.5  
 mM for 2 h) showed slight increases in surface roughness to  
 around 0.4 nm RMS, with complete loss of the atomic step edge  
 features. It was then found that short reactions using more dilute  
 solutions than normal (around 0.01 mM) left the surface sparsely  
 reacted, enabling small vertical islands to be visualized (Figure  
 4a and b). A series of diazonium salts of different lengths were  
 reacted with the flat surfaces to systematically observe these  
 molecular features. Surfaces made with dilute solutions of  
 diazonium salts **V** (observed height approximately 0.7 nm,  
 although at this short length confusion with step edge features  
 and defects is likely), **VI** (observed height approximately 1.5  
 nm), and **II** (observed height approximately 2.0 nm) showed  
 these features consistently, with vertical heights corresponding  
 to single perpendicular molecular lengths. The lateral dimension  
 of the islands is limited by the radius of curvature of the AFM  
 tip, which was typically around 30–40 nm in our images.  
 Although AFM does not give chemical information within the  
 images, given the XPS spectra that show the molecular  
 signatures and no detectable Si oxide, it is plausible to affirm  
 that the features are nucleation sites for film growth and not  
 merely etch pits or oxide.

The exceptional chemical stability of the layers is indirect  
 evidence of covalent bonding. Samples of the various substrates  
 were reacted with **II**, exposed to various cleaning or etching  
 treatments, and analyzed with ellipsometry and XPS. Pd samples  
 reacted with **II** showed no loss of the molecular layers upon  
 sonication in  $\text{CH}_3\text{CN}$  (10 min). If the molecules were simply  
 physisorbed on the surface, this treatment would likely remove  
 most of the organic residue. Similarly reacted GaAs samples  
 were resistant to concentrated HCl etching solution (5 min),  
 30% aqueous citric acid etch solution, and concentrated  $\text{NH}_4\text{-}$   
 $\text{OH}$  followed by sonication in  $\text{CH}_3\text{CN}$ . Silicon samples reacted  
 with **II** were resistant to 7:1 buffered oxide etch solution (5  
 min), followed by pH 12 KOH solution at 25 °C (5 min),

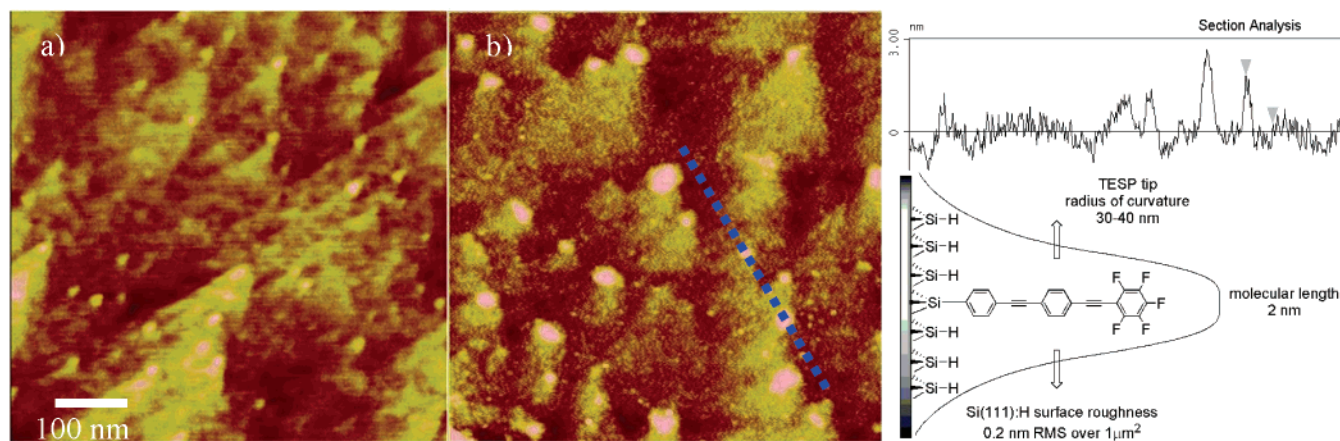
(30) Allongue, P.; de Villeneuve, C. H.; Morin, S.; Boukherroub, R.; Wayner,  
 D. D. M. *Electrochim. Acta* **2000**, *45*, 4591.



**Figure 2.** XPS spectra of reacted samples with monolayer thickness. (a) Spectrum of the C 1s region of the Pd sample reacted with **II**, taken at a 45° takeoff angle. The small peak at 288 eV is due to the pentafluorinated phenyl ring. (b) The spectrum of the Si 2p region of n<sup>2+</sup>-type Si(111) reacted with **II**, taken at a 30° takeoff angle, has a clear 2p<sup>1/2</sup>–2p<sup>3/2</sup> doublet and is free of the oxidation signal normally seen at around 103 eV.



**Figure 3.** CV scans of reacted samples using a 0.01 M Fe(CN)<sub>6</sub><sup>3/4-</sup> redox couple in 0.1 M KClO<sub>3</sub>, with a 1 cm<sup>2</sup> area exposed. (a) Pd sample reacted with **II** (solid line) as compared to clean Pd (dashed line). (b) n<sup>2+</sup>-type Si(111) wafer reacted with **II** (solid line) as compared to the Si(111):H surface (dashed line).



**Figure 4.** Tapping mode AFM images of Si(111) surfaces before and after reaction with diazonium salt **II**. Scale bar is approximate. (a) Hydride-terminated Si(111) sample showing clear atomic step edges and RMS roughness of 0.2 nm over 1 μm<sup>2</sup>. The vertical height of specklike features at step edge tips is less than 0.4 nm. (b) Si(111):H sample reacted for 15 min with 0.5 mM diazonium compound **II** shows initial growth of perpendicular molecules on step edges. The vertical height of the island is approximately 2.0 nm (Section Analysis, based on dashed blue line) measured from the terrace side of the feature. The lateral resolution of the molecular features is limited by the radius of curvature of the AFM tip, as depicted in the scheme.

262 followed by sonication (10 min) in CH<sub>3</sub>CN, CH<sub>2</sub>Cl<sub>2</sub>, or acetone.  
 263 Because of the chemical endurance of the surface–molecule  
 264 bonding, there was little or no loss of the chemisorbed molecular  
 265 species or substantial oxidation of the substrate from any of  
 266 these treatments.

267 Ellipsometric thickness measurements on monolayer films,  
 268 FTIR spectroscopy, and AFM microscopy all provide evidence  
 269 that implies that near-vertically oriented molecules are on the

Si(111) surface. This is consistent with a covalent attachment 270  
 between the aryl groups and the surface that would not allow 271  
 for a large degree of deformation. XPS spectra show a low 272  
 degree of chemical contamination within the attached layers and 273  
 at the critical surface–molecule interface. When combined with 274  
 chemical tests that verify the robustness of the attachment at 275  
 that interface, an overall review of the data is consistent with 276  
 our model of covalently bound monolayers in high coverage 277

278 on the surfaces in question. Now, we must use this model to  
279 justify our theory of how this reaction may activate the  
280 diazonium salts and form the layers.

281 Determining a consistent mechanism of the activation of the  
282 diazonium compounds is complicated by the broad chemical  
283 and physical differences between the metal, elemental semi-  
284 conductor, and binary semiconductor materials used in this  
285 study. It is tempting, especially when considering the hydridic  
286 Si(111):H surface, to propose a cation exchange or charge  
287 injection mechanism for the aryl–surface bond-forming reaction.  
288 This might be qualitatively similar to charge injection from the  
289 ferrocenium cation as a surface activation method.<sup>31</sup> In such a  
290 scheme (Scheme 1), elimination of N<sub>2</sub> from the aryl diazenyl  
291 radical would give an aryl cation intermediate, which would  
292 attack the Si(111):H surface, and then eliminate a proton and  
293 the counterion as HBF<sub>4</sub>. However, reactions of diazonium salts  
294 with silanes,<sup>32</sup> that likely do proceed via the aryl cation, tend  
295 to simply abstract hydride and form reduced aromatics and silyl  
296 halides. Although the hydride abstraction mechanism is a  
297 possibility, and would explain the very high degree of Si–H  
298 loss seen in FTIR spectra, inorganic surface fluoride from the  
299 counterion is something that we have not systematically  
300 observed on any of our surfaces. It also would not explain the  
301 formation of Si–C or other organometallic bonds. Finally, such  
302 a mechanism would not show significant sensitivity to the  
303 presence of BHT. As the major component of spontaneous  
304 diazonium activation, hydride abstraction can be ruled out.

305 Combellas and coauthors<sup>15</sup> have proposed an OCP-based  
306 mechanism for the spontaneous reduction of diazonium salts  
307 on a carbonaceous material made from an electrochemically  
308 reduced PTFE electrode surface. Is such a mechanism plausible  
309 for materials such as Si, GaAs, and Pd? The tendency of  
310 metastable surfaces such as Si(111):H to oxidize spontaneously,  
311 at OCP, provides a complementary means of reduction, as seen  
312 in Wade and Chidsey's experiments on the OCP-driven reduc-  
313 tion of dioxygen to superoxide in fluoride solution.<sup>23</sup> If the OCP  
314 of the Si(111):H surface<sup>33</sup> in contact with 0.5 mM diazonium  
315 salt in CH<sub>3</sub>CN is more negative than the reduction potential of  
316 the diazonium itself, about +0.3 V versus SCE,<sup>34</sup> it is possible  
317 to have the spontaneous reduction. Yet, unlike the dioxygen-  
318 superoxide system or reactions with metal salts,<sup>24</sup> we do not  
319 generally see the expected surface oxidation or major surface  
320 etching that might accompany the spontaneous reduction. The  
321 reverse electron transfer could instead have effects that were  
322 beyond our ability to analyze, such as a roughening of the  
323 opposite etched side or cleaved edges of the silicon wafer or  
324 reaction with a solution impurity species that we could not  
325 detect.

326 Nevertheless, the diazonium salts react with the surfaces and  
327 cleanly eliminate the N<sub>2</sub> and BF<sub>4</sub><sup>-</sup> byproducts from the surface,  
328 leaving no analytical traces on the surface. The effect of BHT  
329 on the multilayer formation implies that aryl radical intermedi-  
330 ates play a significant role in the surface reaction, which would  
331 be a secondary product of spontaneous electron transfer (the  
332 direct product being a short-lived diazenyl radical). This effect

was most dramatic for diazonium assemblies on Pd and Si, and  
less so for the GaAs surface.

This spontaneous diazonium activation reaction offers an  
attractive route to highly passivating, robust monolayers and  
multilayers on many surfaces that allow for strong bonds  
between carbon and surface atoms. A data-encompassing  
explanation for the mechanism calls for an OCP-driven diazo-  
nium activation with aryl radical secondary products attacking  
the surface and forming the bonds. Covalently bound mono-  
layers on Pd, Si, and GaAs offer possibilities for new applica-  
tions in processing, electronic transport, and antistiction coatings  
for polysilicon-based MEMS devices, as well as a platform to  
study through-bond interactions between molecules chemisorbed  
on surfaces and the bulk materials to which they are attached.  
Current work includes improving the long-range order of the  
surface assemblies, determining molecular effects on the  
electronic structure of the interfaces, and adapting molecular  
assemblies with reported negative differential resistance (NDR)  
properties into silicon-based hybrid molecular electronic devices  
to assess molecular versus interfacial-based device behavior.<sup>4,8</sup>

## Experimental Section

**Reagents and Solvents for Surface Reactions.** Acetonitrile (CH<sub>3</sub>-  
CN, 99.5+%) for surface reactions was purchased from Aldrich packed  
under nitrogen in a SureSeal container. CH<sub>3</sub>CN, dichloromethane (CH<sub>2</sub>-  
Cl<sub>2</sub>), ethanol (EtOH), methanol (MeOH), and water used for rinsing  
were purchased at HPLC grade and used without further purification.  
Concentrated ammonium fluoride (NH<sub>4</sub>F) was purchased at VLSI grade  
from J. T. Baker. Concentrated hydrochloric acid (HCl), concentrated  
NH<sub>4</sub>F, concentrated ammonium hydroxide (NH<sub>4</sub>OH), concentrated  
sulfuric acid (H<sub>2</sub>SO<sub>4</sub>), 49% hydrofluoric acid (HF), and 30% hydrogen  
peroxide (H<sub>2</sub>O<sub>2</sub>) were purchased at reagent grade. Before use, all  
diazonium salts were stored under nitrogen in tightly capped vials, in  
the dark at -30 °C.

**Ellipsometric Measurements.** Measurements of surface optical  
constants and molecular layer thicknesses were taken with a single  
wavelength (632.8 nm laser) Gaertner Stokes ellipsometer. The *n* value  
for the clean Pd surface was 1.9, and *k* was -4.2. The *n* value for the  
Si(111):H surface was 3.87, and *k* was -0.04. The *n* value for the  
clean GaAs surface was 3.85, and *k* was -0.2. The surface thickness  
was modeled as a single absorbing layer atop an infinitely thick substrate  
(fixed *n<sub>s</sub>*). The observed error in repeated measurements of the same  
spot was typically 0.2 nm or less.

**Cyclic Voltammetry (CV) Measurements.** Electrochemical char-  
acterization was carried out with a Bioanalytical Systems (BAS CV-  
50W) analyzer. The reference was a saturated calomel electrode (SCE).  
The counterelectrode was a clean Pt wire. The aqueous redox couple  
and electrolyte were 0.01 M Fe(CN)<sub>6</sub><sup>3/4-</sup> in 0.1 M KClO<sub>4</sub>. Ap-  
proximately 1 cm<sup>2</sup> of sample was exposed to solution during CV  
measurements. The scan rate was 100 mV s<sup>-1</sup> from -200 to 600 mV.

**Atomic Force Microscopy (AFM) Measurements.** A Digital  
Instruments Nanoscope IIIa tapping mode instrument was used with  
freshly CHCl<sub>3</sub>-cleaned TESP tips. Images were taken in air without  
using a purge box. Samples were prepared as normal and loaded into  
the AFM within a few minutes of their final rinsing. Samples prepared  
for Figure 4 were reacted for ≤15 min using approximately 0.05 mM  
diazonium solution in CH<sub>3</sub>CN in a glovebox.

**X-ray Photoelectron Spectroscopy (XPS) Measurements.** A  
Physical Electronics (PHI 5700) XPS/ESCA system at 5 × 10<sup>-9</sup> Torr  
was used to take photoelectron spectra. A monochromatic Al X-ray  
source at 350 W was used with an analytical spot size of 1.2 mm<sup>2</sup> and  
a 45° or 30° takeoff angle, with a pass energy of 11.75 eV.

**FTIR Measurements.** A customized analytical system, based on a  
Mattson Research Series bench, was used, whose basic details are

(31) Haber, J. A.; Lauermaun, I.; Michalak, D.; Vaid, T. P.; Lewis, N. S. *J. Phys. Chem. B* **2000**, *104*, 9947.

(32) Nakayama, J.; Yoshida, M.; Simamura, O. *Tetrahedron* **1970**, *26*, 4409.

(33) Zhang, X. G. *Electrochemistry of Silicon and its Oxide*; Kluwer Academic: New York, 2001.

(34) Eloffson, R. M.; Gadallah, F. F. *J. Org. Chem.* **1969**, *34*, 854.

described in a previous publication.<sup>35</sup> FTIR spectra were obtained under an extended dry air purge using a liquid N<sub>2</sub> cooled wide-band MCT detector. External reflection *p*-polarized spectra used 1200 scans at 2 cm<sup>-1</sup> resolution at an 86° angle of incidence. A multipoint baseline correction and H<sub>2</sub>O and CO<sub>2</sub> subtractions in GRAMS/32 are used for qualitative and presentation purposes.

**Surface Preparation and Optical Constants.** Pd samples were deposited by ion mill sputtering onto a 2-in. undoped oxidized Si wafer at 0.1 Å s<sup>-1</sup> until a final thickness of 2000 Å was reached. No surface adhesion layer was used. The Pd samples were reacted within 10 min after coming out of the vacuum chamber, without any surface cleaning. Highly doped 2-in. n-type Si(111) wafers (prime grade, As doped, 0.001–0.005 Ω cm) were first cleaned for 20 min in 2:1 H<sub>2</sub>SO<sub>4</sub>/H<sub>2</sub>O<sub>2</sub> (piranha solution) followed by rinsing copiously with water and drying in a stream of N<sub>2</sub>. The wafer was then hydride-terminated by immersion in N<sub>2</sub>-sparged concentrated (40%) NH<sub>4</sub>F for 15 min, rinsed with water, and dried in a stream of N<sub>2</sub>. Undoped GaAs(100) samples were cut (about 4 cm<sup>2</sup>) from a 3-in. wafer, sonicated in EtOH for 15 min, and UV/O<sub>3</sub> cleaned for 15 min. The oxidized GaAs shards were then treated with concentrated (40%) NH<sub>4</sub>OH for 1 min, followed by a brief rinse in water, then EtOH, and finally a gentle stream of N<sub>2</sub>. XPS experiments on GaAs used shards from a lightly Te-doped GaAs(100) wafer prepared and characterized with the same protocols.

**Reactions with Diazonium Salts.** The cleaned, prepared samples were brought inside a low-oxygen N<sub>2</sub>-atmosphere glovebox (with levels of 1 ppm H<sub>2</sub>O and O<sub>2</sub>). Inside the glovebox, a solution of the diazonium salt was made to 0.5 mM concentration in CH<sub>3</sub>CN, providing enough volume to completely cover the entire sample inside a glass screw-cap Nalgene jar. To adequately cover a 2-in. wafer, at least 10 mL must be prepared. For the smaller shards of GaAs, 5 mL of solution is sufficient. The surface samples are immersed in the diazonium solution, sealed to prevent evaporation, and covered with foil to prevent light exposure. The reaction time was 2 h, although shorter reaction times may be possible. Reaction times longer than 6 h tended to create multilayers up to 3.5–5 nm thick, depending on the molecule that was used (layer thicknesses were determined by ellipsometry). At the end of the reaction, the samples were brought out of the glovebox, rinsed with CH<sub>3</sub>CN and soaked for 5 min (to remove residual diazonium salt), and then rinsed with CH<sub>2</sub>Cl<sub>2</sub> (to remove physisorbed hydrocarbons) and soaked for 1 min. The samples were removed from the CH<sub>2</sub>Cl<sub>2</sub> and then dried thoroughly with N<sub>2</sub>.

**Synthetic Materials and General Synthetic Procedures.** Unless stated otherwise, reactions were performed in dried glassware under dry nitrogen atmosphere. Reagent grade diethyl ether (Et<sub>2</sub>O) and tetrahydrofuran (THF) were distilled from sodium benzophenone ketyl. *N,N*-Diisopropylethylamine (Hünig's base), triethylamine (TEA), and *N,N*-dimethylformamide (DMF) were distilled from calcium hydride. Reagent grade hexanes, CH<sub>2</sub>Cl<sub>2</sub>, MeOH, EtOH, and ethyl acetate (EtOAc) were used without further distillation. Trimethylsilylacetylene (TMSA) was donated by FAR Research. All other commercially available reagents were used as received. Unless noted, reactions were magnetically stirred and monitored by thin-layer chromatography (TLC) using E. Merck silica gel 60 F<sub>254</sub> precoated plates (0.25-mm). In general, the chromatography guidelines reported by Still were followed.<sup>36</sup> Flash chromatography (silica gel) was performed with the indicated solvent systems using silica gel grade 60 (230–400 mesh). <sup>1</sup>H and <sup>13</sup>C NMR spectra were taken at 400 and 100 MHz, respectively, and chemical shifts are reported relative to CD<sub>3</sub>CN (<sup>1</sup>H, 1.96, <sup>13</sup>C, 118.26) except when specified. All new compounds were named using AutoNom v. 2.2 under license of Beilstein Informationssysteme.

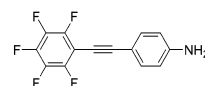
**General Procedure for the Coupling of a Terminal Alkyne with an Aryl Halide Utilizing a Palladium–Copper Cross-Coupling (Castro–Stephens/Sonogashira Protocol).**<sup>37,38</sup> To an oven-dried screw

cap tube or a round-bottom flask and a magnetic stir bar were added the aryl halide, bis(triphenylphosphine)palladium(II) dichloride (5 mol % based on aryl halide), and copper(I) iodide (10 mol % based on aryl halide). The vessel was then sealed with a rubber septum, evacuated, and backfilled with nitrogen (3×). A cosolvent of THF was added followed by Hünig's base. The terminal alkyne was added, and the reaction was heated, if necessary, until complete. The reaction vessel was cooled to room temperature and quenched with water. The organic layer was diluted with CH<sub>2</sub>Cl<sub>2</sub> and washed with a saturated solution of NH<sub>4</sub>Cl (3×). The combined aqueous layers were extracted with CH<sub>2</sub>Cl<sub>2</sub> (3×). The combined organic layers were dried over anhydrous MgSO<sub>4</sub>, and the solvent was removed in vacuo. The crude product was then purified by flash or column chromatography (silica gel).

**General Procedure for Alkaline Deprotection of Trimethylsilyl-Protected Alkynes.** The TMS-protected alkyne was added to an open round-bottom flask equipped with a stirring bar and a solution of potassium carbonate in MeOH or tetrabutylammonium fluoride (TBAF) buffered with a mixture of acetic acid (AcOH) and acetic anhydride (Ac<sub>2</sub>O). THF and CH<sub>2</sub>Cl<sub>2</sub> were added to dissolve the organic compound. The reaction was monitored by TLC every 5 min until deprotection was completed. The reaction was quenched with water and extracted with organic solvents (3×). The combined organic layers were dried over anhydrous MgSO<sub>4</sub>, and the solvent was removed in vacuo. The crude product was then purified by flash chromatography.

**General Procedure for Diazotization of Anilines.**<sup>39</sup> Into an oven-dried round-bottom flask equipped with a magnetic stir bar was added nitrosonium tetrafluoroborate (1.1 equiv per aniline) in the drybox, and the vessel was sealed with a rubber septum. CH<sub>3</sub>CN was added to dissolve the salt and cooled to –30 °C. Separately, into an oven-dried round-bottom flask equipped with a magnetic stir bar was added the aniline that was dissolved in a minimum amount of CH<sub>3</sub>CN. The organic solution was transferred dropwise via cannula, and the temperature was allowed to rise to 0 °C. Et<sub>2</sub>O was slowly added until a precipitate came out from the slurry. The precipitate was collected by filtration, washed with Et<sub>2</sub>O (3×), and dried.

**4-Styrylbenzenediazonium Tetrafluoroborate (I).** To a 25 mL round-bottom flask in a drybox was added NOBF<sub>4</sub> (0.1 g, 0.95 mmol). Acetonitrile (2 mL) was added, and the flask was cooled to –30 °C. A solution of 4-styrylaniline<sup>40</sup> (0.17 g, 0.86 mmol) and BHT (0.19 g, 0.86 mmol) in acetonitrile (5 mL) was added dropwise. The reaction was allowed to warm to –5 °C over 20 min. Et<sub>2</sub>O (10 mL) was added, and the precipitate was filtered. The title compound was purified by reprecipitating from CH<sub>3</sub>CN (3 mL) with ether (15 mL) to yield 0.82 g (34%) of the desired compound. IR (KBr): 3360, 3108, 2271, 1654, 1581, 1497, 1497, 1421, 1079 cm<sup>-1</sup>. <sup>1</sup>H NMR (400 MHz, CD<sub>3</sub>CN): δ 8.50 (d, *J* = 8.8 Hz, 2H), 8.39 (d, *J* = 8.8 Hz, 2H), 8.13 (d, *J* = 8.8 Hz, 2H), 7.77 (d, *J* = 8.8 Hz, 2H), 7.65 (d, *J* = 16.8 Hz, 1H), 7.53 (d, *J* = 16.8 Hz, 1H). <sup>13</sup>C NMR (100 MHz, CD<sub>3</sub>CN): δ 159.8, 155.3, 150.1, 133.3, 133.7, 130.0, 112.9, 112.22.



**4-Pentafluorophenylethynylaniline.** Following the Sonogashira coupling protocol, pentafluorobromobenzene (9.6 mL, 77 mmol), PdCl<sub>2</sub>(PPh<sub>3</sub>)<sub>2</sub> (2.7 g, 3.9 mmol, 5 mol %), and CuI (1.5 g, 7.7 mmol, 10 mol %) were dissolved in THF (100 mL). Hünig's base (53 mL, 307 mmol) was added, followed by 4-ethynylaniline<sup>41</sup> (9 g, 77 mmol), and the mixture was left overnight at 75 °C. Purification by flash chromatography (CH<sub>2</sub>Cl<sub>2</sub> eluent) afforded the desired product (4.4 g, 21% yield) as a dark yellow solid. IR (KBr): 3482, 3394, 2206, 1610, 1501, 1446, 515

(35) Parikh, A. N.; Allara, D. L. *J. Chem. Phys.* **1992**, *96*, 927.

(36) Still, W. C.; Kahn, M.; Mitra, A. *J. Org. Chem.* **1978**, *43*, 2923.

(37) Sonogashira, K.; Tohda, Y.; Hagihara, N. *Tetrahedron Lett.* **1975**, *50*, 4467.

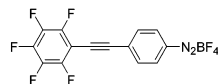
(38) Stephens, R. D.; Castro, C. E. *J. Org. Chem.* **1963**, *28*, 3313.

(39) Kosynkin, D. V.; Tour, J. M. *Org. Lett.* **2001**, *3*, 993.

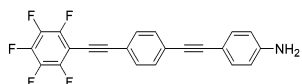
(40) Ziegler, C. B.; Heck, R. F. *J. Org. Chem.* **1978**, *43*, 2941.

(41) Mongin, O.; Gossauer, A. *Tetrahedron* **1997**, *53*, 6835.

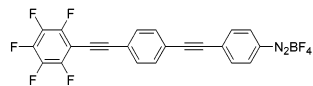
516 1290, 1176, 1133, 1033  $\text{cm}^{-1}$ .  $^1\text{H}$  NMR (400 MHz,  $\text{CDCl}_3$   $\delta$  7.27):  
 517 7.37 (m, 2H), 6.65 (m, 2H), 3.93 (br s, 2H).  $^{13}\text{C}$  NMR (100 MHz,  
 518  $\text{CDCl}_3$   $\delta$  77.23): 148.0, 133.6, 114.8, 110.8, 103.0, 71.4. HRMS calc'd  
 519 for  $\text{C}_{14}\text{H}_6\text{F}_5\text{N}$ , 283.0420; found, 283.0423.



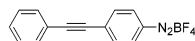
520 **4-Pentafluorophenylethynylbenzenediazonium Tetrafluoroborate**  
 521 (VI). Following the general procedure for diazotization, 4-pentafluoro-  
 522 phenylethynylaniline (400 mg, 1.4 mmol) was dissolved in  $\text{CH}_3\text{CN}$   
 523 (19 mL) and submitted under reaction with  $\text{NOBF}_4$  (182 mg, 1.5 mmol).  
 524 The desired product (487 mg, 91%) was isolated as a light yellow solid.  
 525 IR (KBr): 3421, 2950, 2883, 2356, 2161, 1475, 1372, 1244, 1183  $\text{cm}^{-1}$ .  
 526  $^1\text{H}$  NMR (400 MHz,  $(\text{CD}_3)_2\text{SO}$   $\delta$  2.54):  $\delta$  8.75 (d,  $J = 9.2$  Hz, 2H),  
 527 8.21 (d,  $J = 9.2$  Hz, 2H).  $^{13}\text{C}$  NMR (100 MHz,  $(\text{CD}_3)_2\text{SO}$   $\delta$  40.4):  
 528 135.1, 134.4, 133.0, 117.8, 99.0, 82.9.



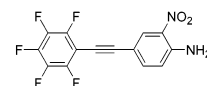
529 **4-(4-(4-Pentafluorophenylethynyl)phenylethynyl)aniline.** 4-(4-Io-  
 530 dophenylethynyl)aniline<sup>42</sup> (0.31 g, 1.0 mmol),  $\text{PdCl}_2(\text{PPh}_3)_2$  (28 mg,  
 531 0.04 mmol),  $\text{CuI}$  (8 mg, 0.04 mmol), TEA (2 mL), THF (2 mL), and  
 532 pentafluorophenylacetylene (0.28 g, 1.5 mmol) were used following  
 533 the general procedure for couplings. The tube was capped and stirred  
 534 at room temperature for 14 h. Flash column chromatography (1:1  
 535 hexanes: $\text{CH}_2\text{Cl}_2$ ) afforded the desired product as light yellow needles  
 536 (0.16 g, 43% yield). IR (KBr): 3417, 2206, 1623, 1595, 1526, 1497,  
 537 1446, 1298, 1138  $\text{cm}^{-1}$ .  $^1\text{H}$  NMR (400 MHz,  $\text{CDCl}_3$  7.27):  $\delta$  7.47 (m,  
 538 4H), 7.34 (m,  $J = 8.7, 2.5, 1.8, 0.6$  Hz, 2H), 6.64 (m,  $J = 8.7, 2.5, 1.8,$   
 539 0.6 Hz, 2H), 3.85 (br s, 2H).  $^{13}\text{C}$  NMR (100 MHz,  $\text{CDCl}_3$  77.23):  $\delta$   
 540 147.2, 133.3, 131.9, 131.8, 131.5, 125.6, 120.5, 114.9, 112.2, 93.3,  
 541 87.1, 74.6.



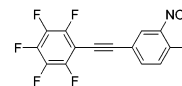
542 **4-(4-(4-Pentafluorophenylethynyl)phenylethynyl)benzenediazo-**  
 543 **nium Tetrafluoroborate (II).** Following the general diazotization  
 544 procedure, 4-(4-pentafluorophenylethynyl)phenylethynylaniline (0.15  
 545 g, 0.04 mmol) was treated with  $\text{NOBF}_4$  (52 mg, 0.52 mmol) in  $\text{CH}_3$ -  
 546  $\text{CN}$  (4 mL) and sulfolane (4 mL). After the mixture was dried in vacuo,  
 547 the desired product was isolated (0.12 g, 64% yield) as a yellow solid.  
 548 IR (KBr): 3106, 2275, 2214, 1576, 1526, 1502, 1078, 989, 854, 832  
 549  $\text{cm}^{-1}$ .  $^1\text{H}$  NMR (400 MHz,  $(\text{CD}_3)_2\text{SO}$   $\delta$  2.54):  $\delta$  8.71 (m, 2H), 8.15  
 550 (m, 2H), 7.74 (m, 4H).  $^{13}\text{C}$  NMR (100 MHz,  $(\text{CD}_3)_2\text{SO}$   $\delta$  40.4):  $\delta$   
 551 133.8, 133.6, 133.0, 132.6, 132.2, 122.1, 114.9, 100.1, 98.3, 89.8, 75.5.



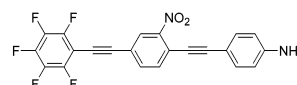
552 **4-Phenylethynylbenzenediazonium Tetrafluoroborate (III).** Fol-  
 553 lowing the general diazotization procedure, 4-phenylethynylaniline<sup>43</sup>  
 554 (0.57 g, 3 mmol) was treated with  $\text{NOBF}_4$  (0.36 g, 3.15 mmol) in  $\text{CH}_3$ -  
 555  $\text{CN}$  (20 mL). Yellow needles of the desired product were precipitated  
 556 with ether (0.75 g, 86% yield). IR (KBr): 3100, 2293, 2216, 1577,  
 557 1415, 1071, 1033  $\text{cm}^{-1}$ .  $^1\text{H}$  NMR (400 MHz,  $\text{CD}_3\text{CN}$ ):  $\delta$  8.86 (m,  $J$   
 558 = 8.7, 2.4, 1.7, 0.5 Hz, 2H), 8.16 (m,  $J = 8.7, 2.4, 1.7, 0.5$  Hz, 2H),  
 559 7.49 (m, 3H), 7.67 (m, 2H).  $^{13}\text{C}$  NMR (100 MHz,  $\text{CD}_3\text{CN}$ ):  $\delta$  137.1,  
 560 134.6, 134.0, 133.1, 131.4, 129.8, 121.9, 114.3, 101.5, 88.2.



**2-Nitro-4-pentafluorophenylethynylaniline.** Following the general 561  
 coupling procedure, 4-ethynyl-2-nitroaniline<sup>44</sup> (6.2 g, 38.7 mmol),  $\text{PdCl}_2$ - 562  
 $(\text{PPh}_3)_2$  (1 g, 1.5 mmol),  $\text{CuI}$  (0.6 g, 3 mmol), and TEA (27 mL, 155 563  
 mmol) were dissolved in THF (50 mL). Pentafluorobromobenzene (19 564  
 g, 77.3 mmol) was added, and the reaction was heated at 70  $^\circ\text{C}$  565  
 overnight. Purification by flash chromatography ( $\text{CH}_2\text{Cl}_2$ ) afforded the 566  
 desired product (3.7 g, 30%) as an orange solid. IR (KBr): 3468, 3364, 567  
 3099, 2469, 2428, 2221, 1933, 1801, 1728, 1631, 1583, 1550, 1413, 568  
 1338, 1284, 1243, 1163, 1117, 1077, 1033  $\text{cm}^{-1}$ .  $^1\text{H}$  NMR (400 MHz, 569  
 $\text{CDCl}_3$  7.27):  $\delta$  8.32 (s, 1H), 7.62 (d,  $J = 8.8, 1\text{H}$ ), 7.53 (br s, 2H), 570  
 7.21 (d,  $J = 8.8, 1\text{H}$ ).  $^{13}\text{C}$  NMR (100 MHz,  $\text{CDCl}_3$  77.23):  $\delta$  147.2, 571  
 138.0, 131.3, 130.1, 120.3, 108.4, 100.8, 71.8, 68.9. HRMS for 572  
 $\text{C}_{14}\text{H}_5\text{F}_5\text{N}_2\text{O}_2$ , 328.0271; found, 328.0273. 573



**Pentafluoro-6-(4-iodo-3-nitrophenylethynyl)benzene.** A solution 574  
 of aniline 2-nitro-4-pentafluorophenylethynylaniline (2.9 g, 9 mmol) 575  
 in  $\text{CH}_3\text{CN}$  (40 mL) was slowly added to  $\text{NOBF}_4$  (1.5 g, 13.5 mmol) in 576  
 $\text{CH}_3\text{CN}$  (10 mL) at  $-20$   $^\circ\text{C}$ . The resulting yellow solution was warmed 577  
 to 0  $^\circ\text{C}$ , stirred for 30 min, and transferred via syringe into a flask 578  
 containing a solution of  $\text{NaI}$  (2.7 g, 18 mmol) and  $\text{I}_2$  (4.5 g, 18 mmol) 579  
 in acetonitrile (50 mL). When the vigorous gas evolution was complete, 580  
 the reaction mixture was diluted with water (500 mL), treated with 581  
 urea (1.8 g, 30 mmol) and  $\text{Na}_2\text{SO}_3$  (1.3 g, 11 mmol), and extracted 582  
 with ether. The extracts were washed with water (50 mL) and brine 583  
 (50 mL) and were evaporated. The crude product was purified by 584  
 chromatography ( $\text{CH}_2\text{Cl}_2$ ) to give lemon yellow needles (3.5 g, 90% 585  
 yield). IR (KBr): 3093, 2879, 2629, 2428, 2229, 1940, 1780, 1594, 586  
 1518, 1501, 1443, 1356, 1266, 1151, 1036, 1017  $\text{cm}^{-1}$ .  $^1\text{H}$  NMR (400 587  
 MHz,  $\text{CDCl}_3$ ):  $\delta$  8.07 (d,  $J = 8.0$  Hz, 1H), 8.02 (d,  $J = 1.6$  Hz, 1H), 588  
 7.42 (dd,  $J = 8.4, 2.0$  Hz, 1H).  $^{13}\text{C}$  NMR (100 MHz,  $\text{CDCl}_3$ ):  $\delta$  165.9, 589  
 142.4, 135.8, 128.3, 123.2, 117.7, 89.6, 87.8. HRMS for  $\text{C}_{14}\text{H}_3\text{F}_5\text{INO}_2$ , 590  
 438.9129; found, 438.9125. 591



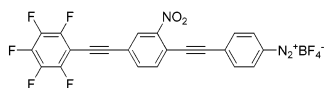
**4-(2-Nitro-4-pentafluorophenylethynyl)phenylethynylaniline.** 592  
 4-Ethynylaniline (0.28 g, 2.4 mmol), bis(triphenylphosphine)palladium- 593  
 (II) dichloride (70 mg, 0.1 mmol), copper(I) iodide (19 mg, 0.1 mmol), 594  
 Hünig's base (0.51 g, 4.0 mmol), THF (4 mL), and 1-iodo-2-nitro-4- 595  
 pentafluorophenylethynylbenzene (0.87 g, 2.0 mmol) were used fol- 596  
 lowing the general procedure for couplings. The bright red slurry formed 597  
 after 14 h of stirring at room temperature was evaporated in vacuo, 598  
 suspended in  $\text{CH}_2\text{Cl}_2$  (10 mL), and filtered. The filter cake was washed 599  
 with the same solvent (15 mL), dried, and recrystallized from THF- 600  
 heptane to afford red silky needles (0.74 g, 87% yield). IR (KBr): 3505, 601  
 3401, 2200, 1624, 1597, 1538, 1524, 1496, 1444, 1351, 1136, 985  $\text{cm}^{-1}$ . 602  
 $^1\text{H}$  NMR (400 MHz,  $(\text{CD}_3)_2\text{SO}$ , 2.54):  $\delta$  8.26 (d,  $J = 1.4$  Hz, 1H), 603  
 7.87 (dd,  $J = 8.1, 1.4$  Hz, 1H), 7.76 (d,  $J = 8.4$  Hz, 1H), 7.24 (d,  $J =$  604  
 8.4 Hz, 1H), 6.59 (d,  $J = 8.4$  Hz), 5.88 (s, 2H).  $^{13}\text{C}$  NMR (100 MHz, 605  
 $(\text{CD}_3)_2\text{SO}$ , 40.4):  $\delta$  151.0, 148.46, 135.6, 134.1, 133.5, 127.5, 119.7, 606  
 119.3, 113.6, 106.4, 102.9, 98.4, 83.1, 76.5. 607

**4-(2-Nitro-4-pentafluorophenylethynyl)phenylethynyl)benzene-** 608  
**diazonium Tetrafluoroborate (IV).** Following the general diazotization 609  
 procedure, 4-(2-nitro-4-pentafluorophenylethynyl)phenylethynylaniline 610

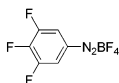
(42) Endo, Y.; Songkram, C.; Yamasaki, R.; Tanatani, A.; Kagechika, H.; Takaishi, K.; Yamaguchi, K. *J. Organomet. Chem.* **2002**, *48*, 657.

(43) Price, D. W., Jr.; Tour, J. M. *Tetrahedron* **2003**, *59*, 3131.

(44) Dirk, S. M.; Price, D. W.; Chanteau, S. H.; Kosynkin, D. V.; Tour, J. M. *Org. Lett.* **2001**, *3*, 5109.



611 (0.42 g, 1 mmol) was treated with NOBF<sub>4</sub> (1.4 g, 1.2 mmol) in CH<sub>3</sub>-  
 612 CN (20 mL) and sulfolane (20 mL). The product was precipitated with  
 613 Et<sub>2</sub>O (200 mL) and recrystallized from CH<sub>3</sub>CN to give orange needles  
 614 (0.26 g, 51% yield). IR (KBr): 3106, 2284, 2214, 15178, 1517, 1444,  
 615 1349, 1291, 1074 cm<sup>-1</sup>. <sup>1</sup>H NMR (400 MHz, CH<sub>3</sub>CN): 8.61 (d, *J* =  
 616 2.4 Hz, 1H), 8.56 (m, 2H), 8.36 (dd, *J* = 8.8, 2.4 Hz, 1H), 8.06 (m,  
 617 2H), 7.94 (d, *J* = 8.8 Hz, 1H) δ. <sup>13</sup>C NMR (100 MHz, CH<sub>3</sub>CN): δ  
 618 149.0, 136.5, 135.4, 134.8, 133.7, 130.9, 128.8, 126.1, 125.8, 115.4,  
 619 96.8, 93.4.



620 **3,4,5-Trifluorobenzenediazonium Tetrafluoroborate (V).** Fol-  
 621 lowing the general procedure for diazotization, 3,4,5-trifluoroaniline

(300 mg, 2 mmol) was dissolved in CH<sub>3</sub>CN (2 mL) and treated with  
 622 NOBF<sub>4</sub> (262 mg, 2.2 mmol). The desired product (350 mg, 71%) was  
 623 isolated as a pale yellow solid. IR (KBr): 3360, 3112, 2285.30, 2222,  
 624 1582, 1496, 1524, 1444, 1069 cm<sup>-1</sup>. <sup>1</sup>H NMR (400 MHz, CD<sub>3</sub>CN): δ  
 625 8.47 (m). <sup>13</sup>C NMR (100 MHz, CD<sub>3</sub>CN): δ 121.5, 121.2.  
 626

**Acknowledgment.** This work was funded by the Defense  
 627 Advanced Research Projects Agency, the Army Research Office,  
 628 and the Office of Naval Research. Paul A. W. van der Heide  
 629 (University of Houston, MRSEC) is thanked for assistance with  
 630 XPS measurements. Dr. I. Chester (FAR Research, Inc.) is  
 631 thanked for providing trimethylsilylacetylene used in the  
 632 syntheses of the diazonium compounds.  
 633

**Supporting Information Available:** XPS spectra of samples  
 634 reacted with fluorinated and nonfluorinated diazonium salts, and  
 635 an FTIR spectrum of the Si(111):H surface (PDF). This material  
 636 is available free of charge via the Internet at <http://pubs.acs.org>.  
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JA0383120  
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